



浙江芯芯电子有限公司
ZHEJIANG XINXIN ELECTRICAL CO., LTD.

产品规格书

Specification of Products

产品名称：可控硅模块

产品型号：MFC110A

浙江芯芯电子有限公司

ZHEJIANG XINXIN ELECTRICAL CO., LTD.

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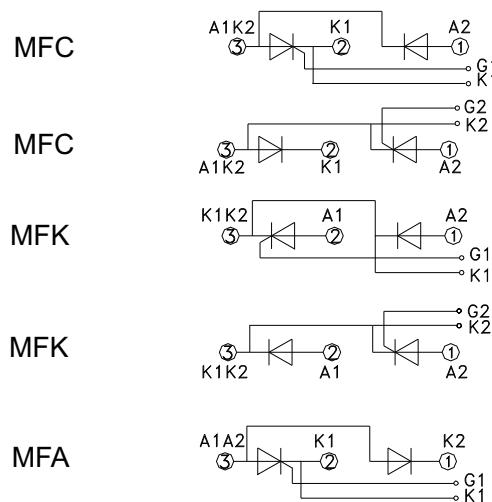
<http://www.zjxxdz1.com>

| 拟制 | 审核 | 核准 |
|-----|-----|-----|
| 丁国盛 | 李园利 | 麻伟阳 |

版本号：04 更新日期：2022.6.28

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | T_J (°C) | VALUE | | | UNIT |
|--------------------------------------|--|---|------------|-------|------|---------------------------------------|---------------------------|
| | | | | Min | Type | Max | |
| $I_{T(AV)}$ $I_{F(AV)}$ | Mean on-state current | 180° half sinewave 50Hz Single side cooled, $T_c=85^\circ\text{C}$ | 125 | | | 110 | A |
| $I_{T(\text{RMS})}$ | RMS on-state current | Single side cooled, $T_c=85^\circ\text{C}$ | 125 | | | 173 | A |
| V_{DRM} V_{RRM} | Repetitive peak off-state voltage Repetitive peak reverse voltage | $V_{\text{DRM}} \& V_{\text{RRM}}$ tp=10ms $V_{\text{DSM}} \& V_{\text{RSM}} = V_{\text{DRM}} \& V_{\text{RRM}} + 200\text{V}$ respectively | 125 | 600 | | 1600 | V |
| I_{DRM} I_{RRM} | Repetitive peak current | at V_{DRM} at V_{RRM} | 125 | | | 12 | mA |
| I_{TSM} | Surge on-state current | 10ms half sinewave | 125 | | | 2.40 | KA |
| I^2t | I^2T for fusing coordination | $V_R=60\%V_{\text{RRM}}$ | | | | 29.3 $\text{A}^2\text{s} \times 10^3$ | |
| V_{TO} | Threshold voltage | | 125 | | | 0.8 | V |
| r_T | On-state slop resistance | | | | | 2.29 | $\text{m}\Omega$ |
| V_{TM} | Peak on-state voltage | $I_{\text{TM}}=330\text{A}$ | 125 | | | 1.4 | V |
| dv/dt | Critical rate of rise of off-state voltage | $V_{\text{DM}}=67\%V_{\text{DRM}}$ | 125 | | | 800 | $\text{V}/\mu\text{s}$ |
| di/dt | Critical rate of rise of on-state current | From 67% V_{DRM} to 330A, Gate source 1.5A $t_r \leq 0.5\text{ }\mu\text{s}$ Repetitive | 125 | | | 100 | $\text{A}/\mu\text{s}$ |
| I_{GT} | Gate trigger current | | 25 | 20 | | 100 | mA |
| V_{GT} | Gate trigger voltage | $V_A=12\text{V}, I_A=1\text{A}$ | | 0.7 | | 2.0 | V |
| I_H | Holding current | | | 20 | | 100 | mA |
| V_{GD} | Non-trigger gate voltage | At 67% V_{DRM} | 125 | | | 0.2 | V |
| $R_{\text{th(j-c)}}$ | Thermal resistance Junction to heatsink | At 180° sine Single side cooled | | | | 0.250 | $^\circ\text{C}/\text{W}$ |
| V_{iso} | Isolation voltage | 50Hz, RM. S, t=1min, $i_{\text{lo}}: 1\text{mA MAX}$) | | 2500 | | | V |
| F_m | Thermal connection torque(M5) | | | | 0.2 | | N.m |
| | Mounting torque(M6) | | | | 0.3 | | N.m |
| T_{stg} | Stored temperature | | | -40 | | 140 | $^\circ\text{C}$ |
| W_t | Weight | | | | 154 | | g |
| Outline | | | | | | | |

OUTLINE DRAWING & CIRCUIT DIAGRAM



Rating and Characteristic

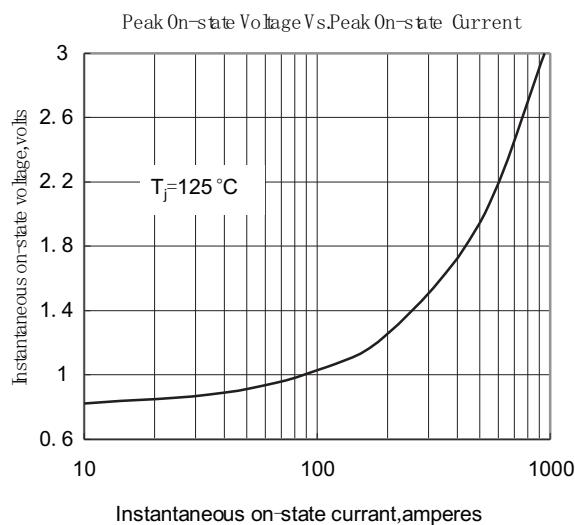


Fig. 1

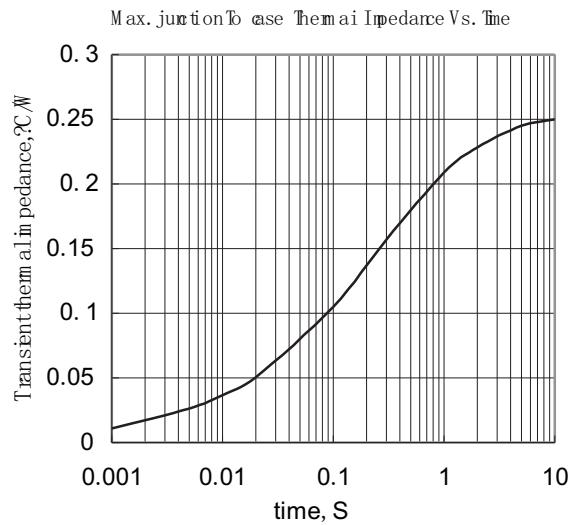


Fig. 2

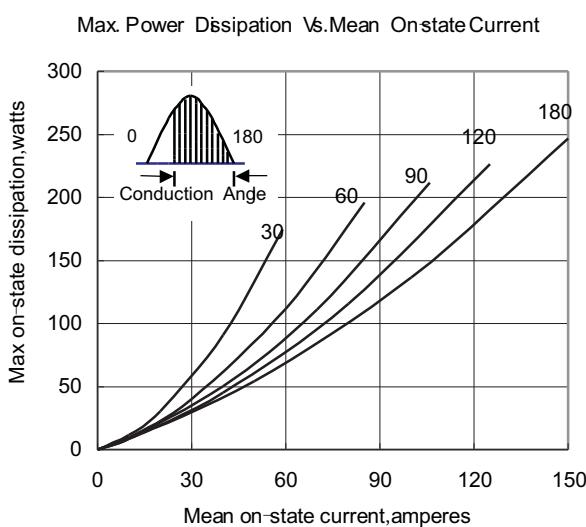


Fig. 3

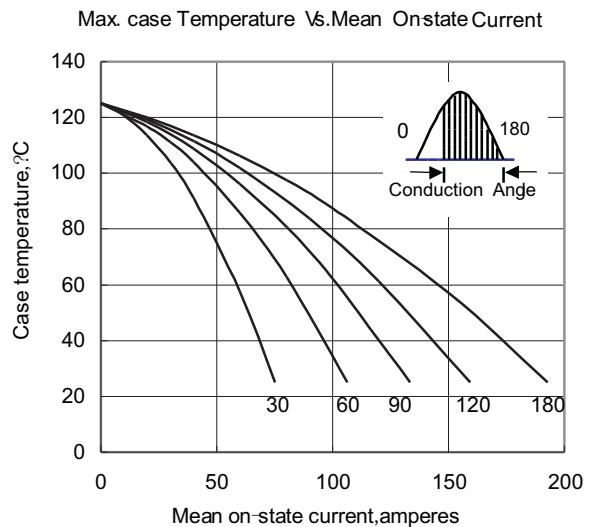


Fig. 4

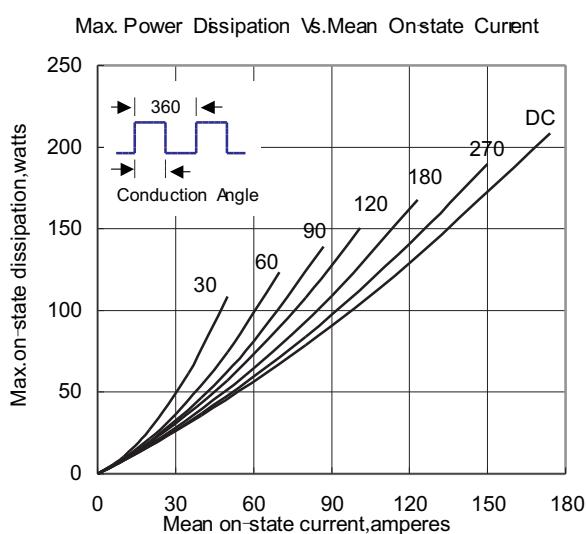


Fig. 5

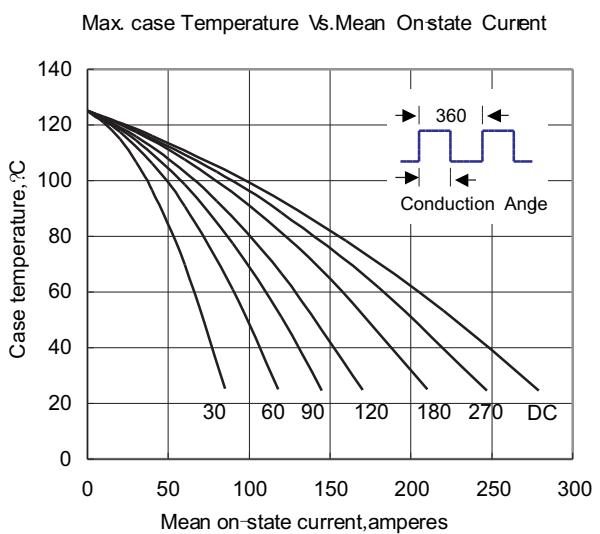


Fig. 6

Rating and Characteristic

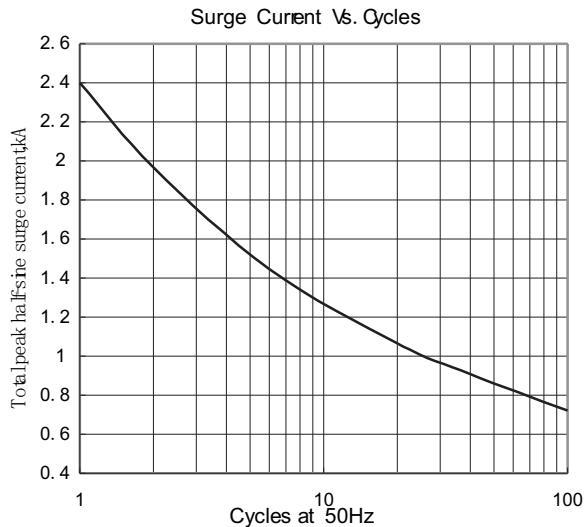


Fig. 7

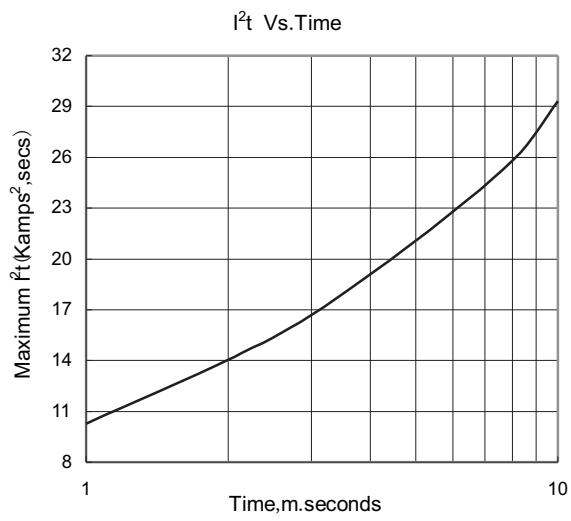


Fig. 8

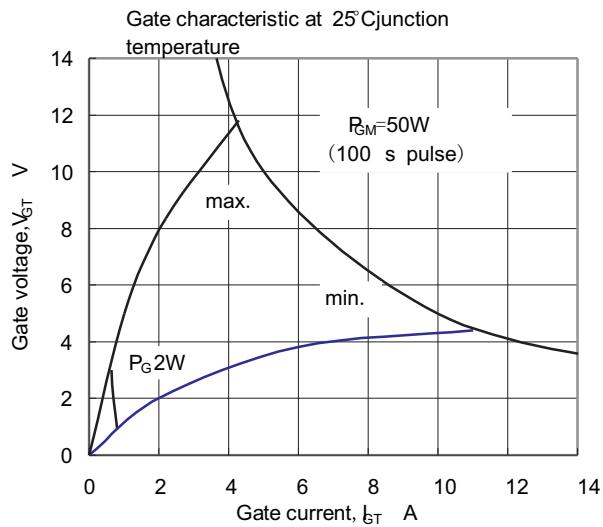


Fig. 9

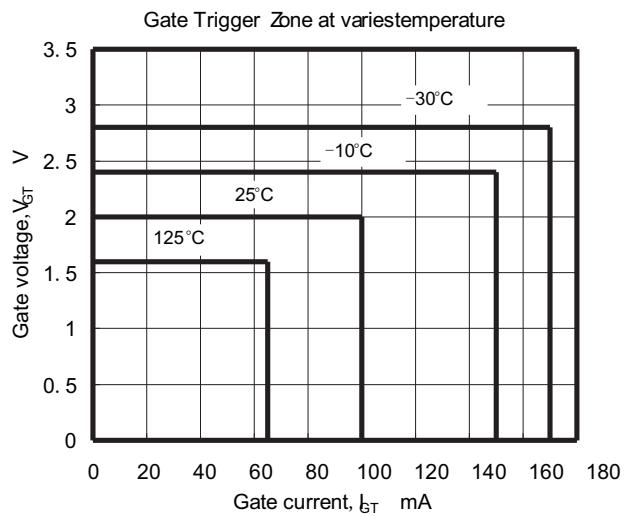


Fig. 10

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